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PUMA 84S32000 - 012/015/020

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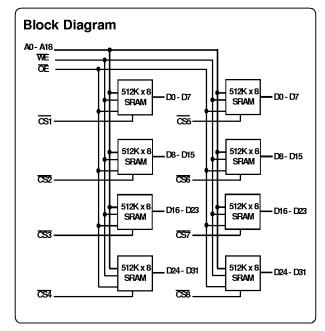
Description

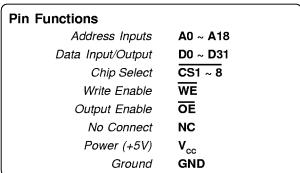
The PUMA 84S32000 is a 32Mbit CMOS High Speed Static RAM organised as 1M x 32 in a JEDEC 84 pin surface mount J-leaded PLCC, available with access times of 12, 15, and 20ns. The output width is user configurable as 8, 16 or 32 bits using eight Chip Selects $(\overline{CS1} \sim 8)$.

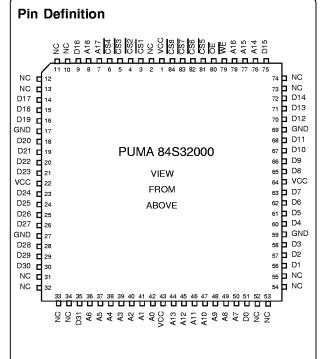
The device features low power standby, multiple ground pins for maximum noise immunity and TTL compatible inputs and outputs. The PUMA 84S32000 offers a dramatic space saving advantage over eight standard 512Kx8 devices.

Features

- Very fast access times of 12/15/20 ns.
- JEDEC 84 'J' leaded plastic Surface Mount Package.
- Single 5V±10% Power supply.
- User Configurable as 8 / 16 / 32 bit wide output.
- Operating Power (32-BIT) 5.28 W (max)
 Low Power Standby CMOS 550 mW (max)
- Fully Static operation.
- · Multiple ground pins for maximum noise immunity.







Package Details

Plastic 84 J-Leaded JEDEC PLCC

DC OPERATING CONDITIONS

Absolute Maximum Ratings (1)						
Parameter	Symbol	Min	Тур	Мах	Unit	
Voltage on any pin relative to V _{ss}	$V_{\top}^{(2)}$	-0.5	-	7.0	V	
Power Dissipation	P_{\scriptscriptstyleT}	-	-	5.0	W	
Storage Temperature	T _{STG}	-65	-	150	°C	

Notes: (1) Stresses above those listed may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

(2) $V_{\scriptscriptstyle T}$ can be -2.0V pulse of less than 8ns.

Recommended Operat	ing Conditions	•					
Parameter		Symbol	Min	Тур	Max	Unit	
Supply Voltage		V _{cc}	4.5	5.0	5.5	٧	
Input High Voltage		V _{IH}	2.2	-	V_{cc} +0.5	V	
Input Low Voltage		$V_{_{IL}}$	-0.3	-	0.8	V	
Operating Temperature	(Commercial)	T_{A}	0	-	70	°C	
	(Industrial)	TAI	-40	-	85	°C	(Suffix I)

DC Electrical Characte	ristics	(V _{CC} =	5V±10%, -40 to 85 C)				
Parameter		Symbol	Test Condition	Min	Тур	max	Unit
I/P Leakage Current Ad	ldress,OE,WE	I	$0V \le V_{IN} \le V_{CC}$	-20	-	20	μΑ
Output Leakage Current		I_{LO}	$\overline{\text{CS}} = V_{\text{IH}_{\text{i}}} V_{\text{I/O}} = \text{GND to } V_{\text{CC}}$	-20	-	20	μΑ
Operating Supply Current	t 32-bit mode	I _{CC32}	Min. Cycle, $\overline{\text{CS}} = \text{V}_{\text{IL}}$, f=f_{MAX} , $\text{I}_{\text{OUT}} = \text{0mA}$	-	-	960	mA
	16-bit mode	I _{CC16}	As Above.	-	-	640	mΑ
	8-bit mode	I _{CC8}	As Above.	-	-	480	mA
Standby Supply Current	TTLlevels	I _{SB1}	$\overline{\text{CS}} = V_{\text{IH}}, f = f_{\text{MAX}}$	-	-	320	mA
	CMOS levels	$I_{_{\mathrm{SB2}}}$	$\overline{\text{CS}} \ge V_{\text{CC}}^{-}0.2V, \ 0.2 \le V_{\text{IN}} \le V_{\text{CC}}^{-}0.2V, \ \text{f=0}$	-	-	100	mΑ
Output Voltage		${\sf V}_{\sf OL}$	$I_{OL} = 8.0 \text{mA}$	-	-	0.4	V
		V_{OH}	$I_{OH} = -4.0 \text{mA}$	2.4	-	-	٧

Notes:

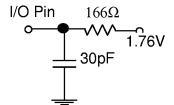
- 1/ Typical values are at V_{cc} =5.0V, T_A =25°C and specified loading. 2/ \overline{CS} above refers to $\overline{CS1}$ ~4 / $\overline{CS5}$ ~8 for 32 bit mode
- At $f=f_{MAX}$ address and data inputs are cycling at maximum frequency.

Capacitance (V _{cc} =5	V±10%,T _A =25°C)		Note: Capacita	nce calculated	, not measu	ıred.
Parameter		Symbol	Test Condition	max	Unit	
Input Capacitance	(Address, OE, WE)	C _{IN1}	V _{IN} = 0V	70	pF	
I/P Capacitance	(Other)	C _{IN2}	$V_{IN} = 0V$	12	pF	
I/O Capacitance	Worst case (8-bit)	$C_{_{I/O}}$	$V_{VO} = 0V$	62	pF	

AC Test Conditions

Output Load

- * Input pulse levels: 0V to 3.0V
- * Input rise and fall times: 3ns
- * Input and Output timing reference levels: 1.5V
- * Output load: see diagram
- * $V_{cc} = 5V \pm 10\%$



Operation Truth Table

<u>cs</u>	ŌĒ	WE	DATA PINS	SUPPLY CURRENT	MODE
Н	Х	Х	High Impedance	I _{SB1} , I _{SB2} , I _{SB3}	Standby
L	L	Н	Data Out	I _{CC32} , I _{CC16} , I _{CC8}	Read
L	Н	L	Data In	I _{CC32} , I _{CC16} , I _{CC8}	Write
L	L	L	Data In	I _{CC32} , I _{CC16} , I _{CC8}	Write
L	Н	Н	High-Impedance	I _{SB1} , I _{SB2} , I _{SB3}	High-Z

Notes : $H = V_{IH}$: $L = V_{IL}$: $X = V_{IH}$ or V_{IL}

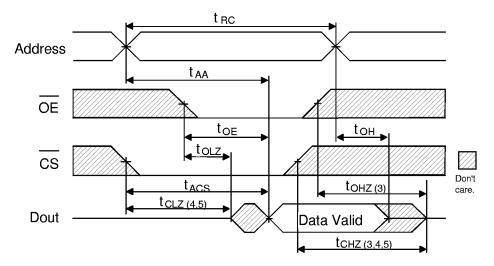
The above table reflects the operation of each of the RAM's on the module. Care should be taken to avoid bus contention on data lines using chip select signals.

AC OPERATING CONDITIONS

Read Cycle								
		012		015		020		
Parameter	Symbol	min	max	min	max	min	max	Unit
Read Cycle Time	t _{RC}	12	-	15	-	20	-	ns
Address Access Time	t _{AA}	-	12	-	15	-	20	ns
Chip Select Access Time	t _{ACS}	-	12	-	15	-	20	ns
Output Enable to Output Valid	t_{\scriptscriptstyleOE}	-	6	-	7	-	9	ns
Output Hold from Address Change	t_{OH}	3	-	3	-	3	-	ns
Chip Selection to Output in Low Z	$t_{\scriptscriptstyle{CLZ}}$	3	-	3	-	3	-	ns
Output Enable to Output in Low Z	$t_{\scriptscriptstyleOLZ}$	0	-	0	-	0	-	ns
Chip Deselection to O/P in High Z	t _{CHZ}	0	6	0	7	0	9	ns
Output Disable to Output in High Z		0	6	0	7	0	9	ns

Write Cycle								
		0	12	(015		020	
Parameter	Symbol	min	max	min	max	min	max	Unit
Write Cycle Time	t _{wc}	12	-	15	-	20	-	ns
Chip Selection to End of Write	t_{cw}	10	-	12	-	15	-	ns
Address Valid to End of Write	t_{AW}	10	-	12	-	15	-	ns
Address Setup Time	t _{as}	0	-	0	-	0	-	ns
Write Pulse Width	t_{WP}	10	-	12	-	12	-	ns
Write Recovery Time	t_{WB}	0	-	0	-	0	-	ns
Write to Output in High Z	t_{wHZ}	0	6	0	7	0	9	ns
Data to Write Time Overlap	t _{DW}	6	-	7	-	9	-	ns
Data Hold from Write Time	\mathbf{t}_{DH}	0	-	0	-	0	-	ns
Output active from end of write	t_{ow}	3	-	3	-	3	-	ns

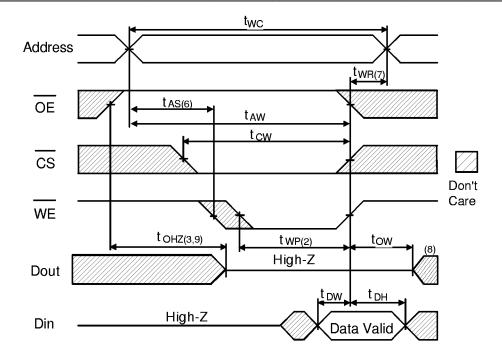
Read Cycle Timing Waveform (1,2)



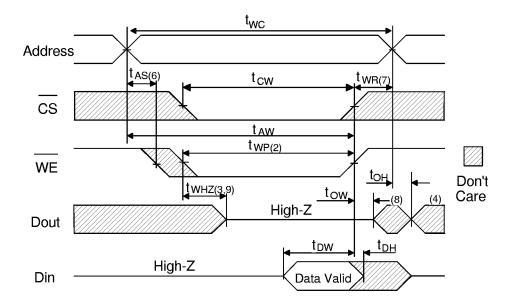
AC Read Characteristics Notes

- (1) WE is High for Read Cycle.
- (2) All read cycle timing is referenced from the last valid address to the first transition address.
- (3) t_{CHZ} and t_{OHZ} are defined as the time at which the outputs achieve open circuit conditions and are not referenced to output voltage levels.
- (4) At any given temperature and voltage condition, t_{CHZ} (max) is less than t_{CLZ} (min) both for a given module and from module to module.
- (5) These parameters are sampled and not 100% tested.

Write Cycle No.1 Timing Waveform(1.4)



Write Cycle No.2 Timing Waveform (1,5)

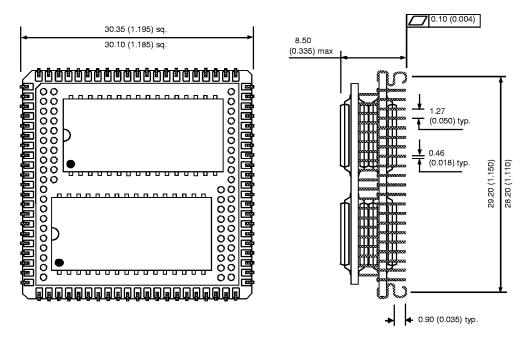


AC Write Characteristics Notes

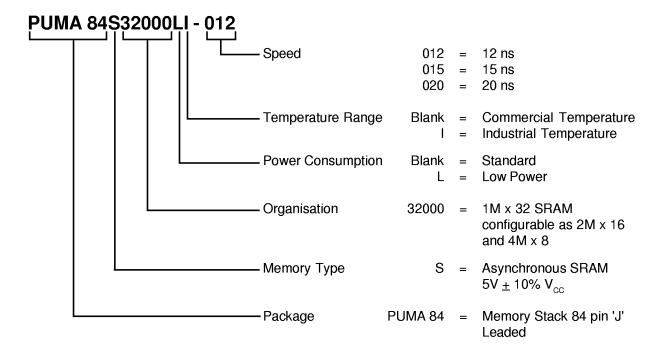
- (1) All write cycle timing is referenced from the last valid address to the first transition address.
- (2) All writes occur during the overlap of \overline{CS} and \overline{WE} low.
- (3) If \overline{OE} , \overline{CS} , and \overline{WE} are in the Read mode during this period, the I/O pins are low impedance state. Inputs of opposite phase to the output must not be applied because bus contention can occur.
- (4) Dout is the Read data of the new address.
- (5) \overline{OE} is continuously low.
- (6) Address is valid prior to or coincident with \overline{CS} and \overline{WE} low, too avoid inadvertant writes.
- (7) $\overline{\text{CS}}$ or $\overline{\text{WE}}$ must be high during address transitions.
- (8) When $\overline{\text{CS}}$ are low: I/O pins are in the output state. Input signals of opposite phase leading to the output should not be applied.
- (9) Defined as the time at which the outputs achieve open circuit conditions and are not referenced to output voltage levels. These parameters are sampled and not 100% tested.

Package Information Dimensions in mm(inches)

Plastic 84 Pin JEDEC Surface mount PLCC



Ordering Information



Note:

Although this data is believed to be accurate the information contained herein is not intended to and does not create any warranty of merchantibility or fitness for a particular purpose.

Our products are subject to a constant process of development. Data may be changed at any time without notice. Products are not authorised for use as critical components in life support devices without the express written approval of a company director.